



Description

The SI7309DN-T1-E3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -60V$ $I_D = -20A$

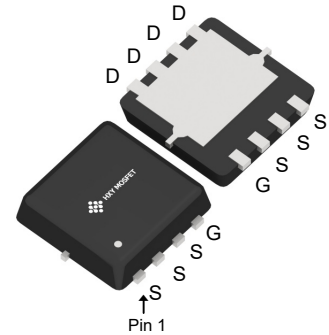
$R_{DS(ON)} < 60m\Omega$ @ $V_{GS} = -10V$

Application

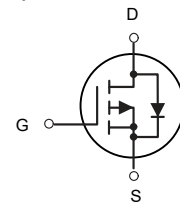
Battery protection

Load switch

Uninterruptible power supply



DFN3X3-8L
(PowerPAK1212-8)



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SI7309DN-T1-E3	DFN3X3-8L (PowerPAK1212-8)	HXY MOSFET	5000

Absolute Maximum Ratings (TC=25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-60	V
VGS	Gate-Source Voltage	±20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-20	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ -10V ¹	-12	A
IDM	Pulsed Drain Current ²	-30	A
EAS	Single Pulse Avalanche Energy ³	18.1	mJ
IAS	Avalanche Current	-13	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	25	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	2	W
TSTG	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.023	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-10A$	---	49	60	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-6A$	---	61	75	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.2	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-15A$	---	12	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V$, $V_{GS}=-4.5V$, $I_D=-15A$	---	6.1	---	nC
Q_{gs}	Gate-Source Charge		---	3.1	---	
Q_{gd}	Gate-Drain Charge		---	1.8	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$, $V_{GS}=-10V$, $R_G=3.3\Omega$, $I_D=-15A$	---	2.6	---	ns
T_r	Rise Time		---	8.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	33.6	---	
T_f	Fall Time		---	6	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1MHz$	---	585	---	pF
C_{oss}	Output Capacitance		---	100	---	
C_{rss}	Reverse Transfer Capacitance		---	85	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-20	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-30	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-15A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	6.1	---	nS
Q_{rr}	Reverse Recovery Charge		---	1.4	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V$, $V_{GS}=-10V$, $L=0.1mH$, $I_{AS}=-19A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

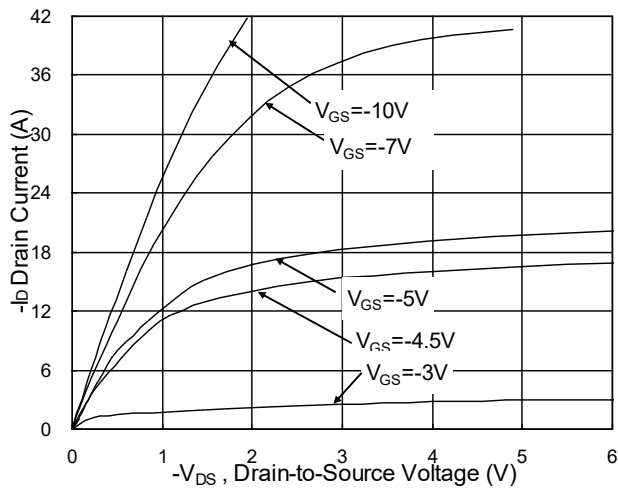


Fig.1 Typical Output Characteristics

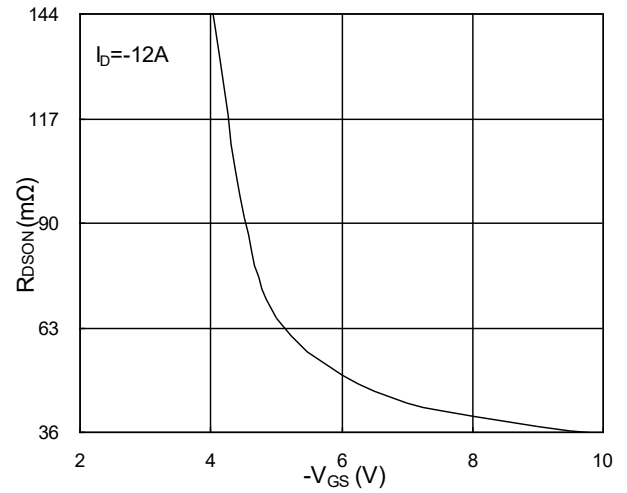


Fig.2 On-Resistance v.s Gate-Source

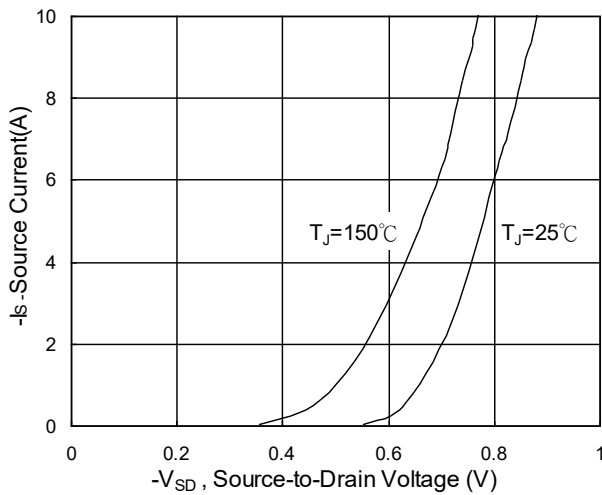


Fig.3 Forward Characteristics Of Reverse

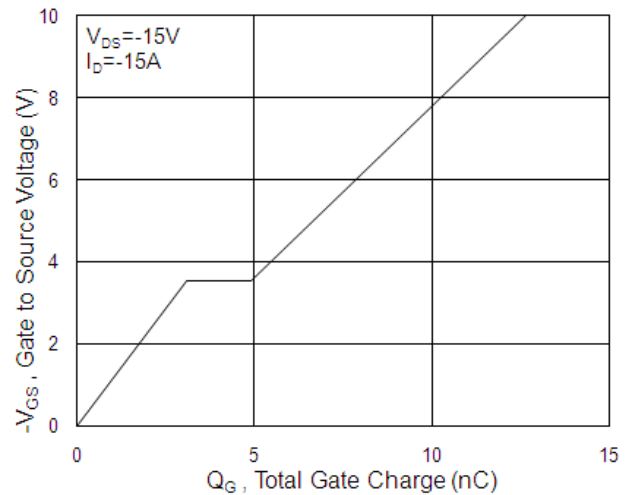


Fig.4 Gate Charge Characteristics

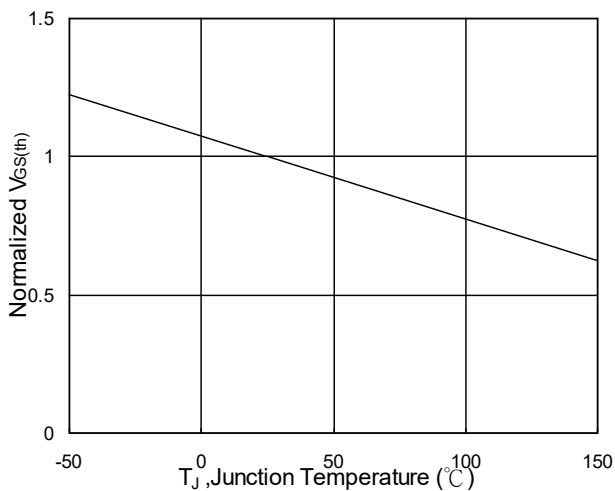


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

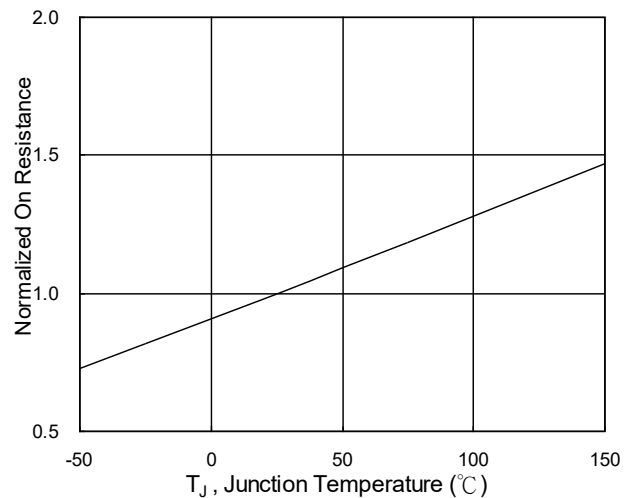


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

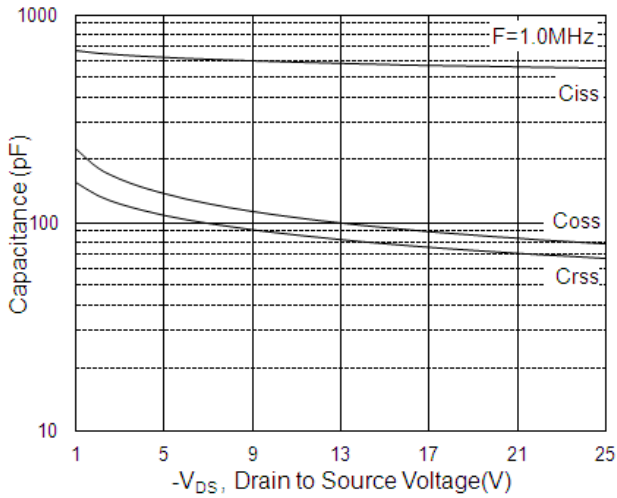


Fig.7 Capacitance

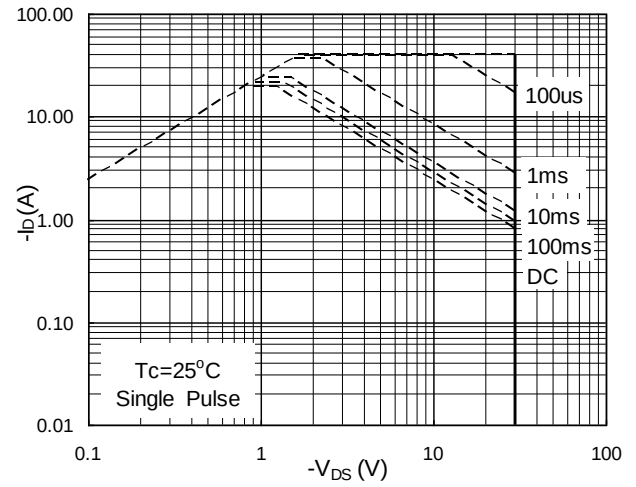


Fig.8 Safe Operating Area

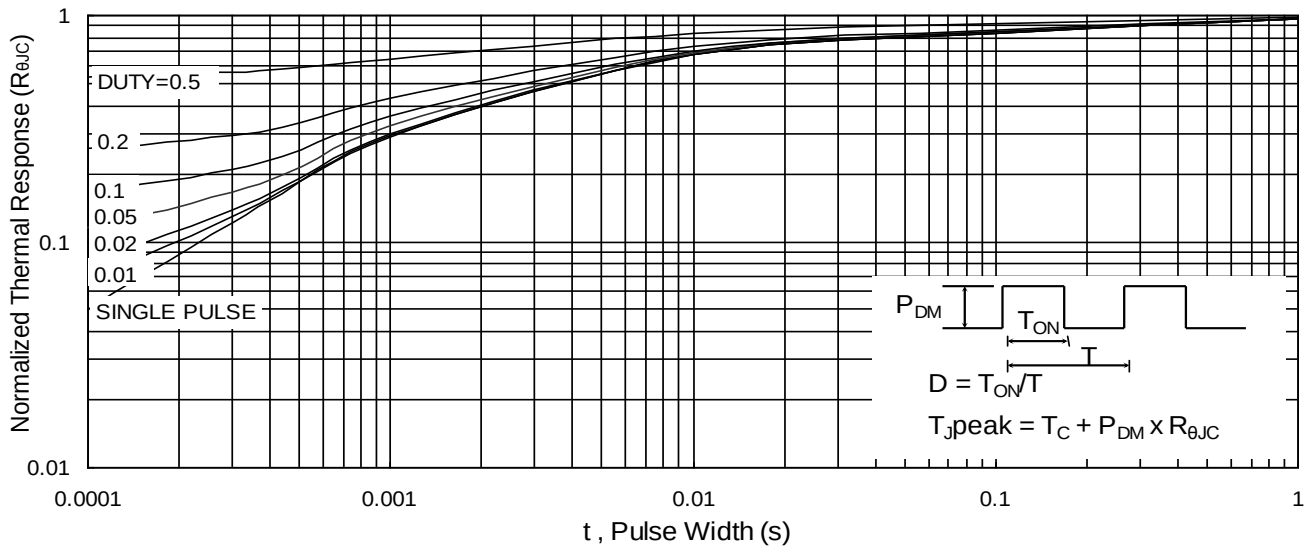


Fig.9 Normalized Maximum Transient Thermal Impedance

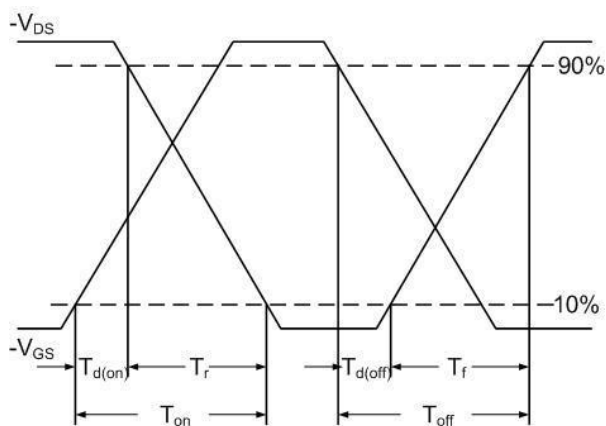


Fig.10 Switching Time Waveform

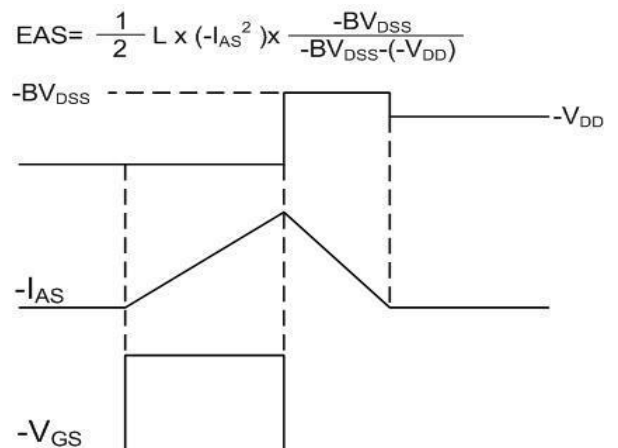
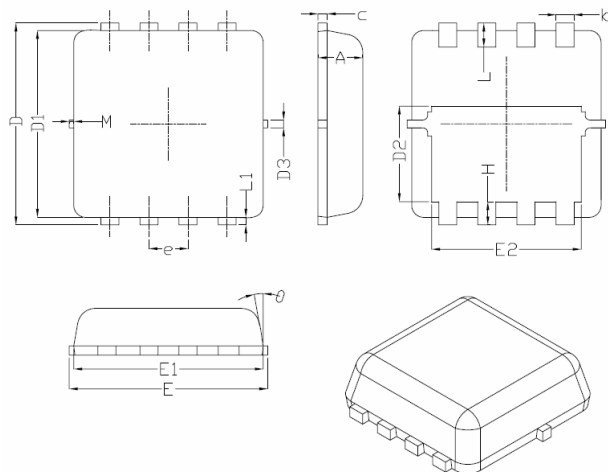


Fig.11 Unclamped Inductive Switching Waveform



DFN3X3-8L(PowerPAK1212-8) Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°



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